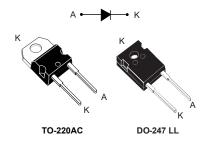


# STPSC15H12

Datasheet

# 1200 V, 15 A power Schottky silicon carbide diode





## **Features**

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- Operating from -40 °C to 175 °C
- Low V<sub>F</sub>
- ECOPACK2 compliant component

## **Applications**

- EV charging stations
- Solar boost converters
- PV converters

## Description

lectronics sales office

The SiC diode, available in TO-220AC and TO-247 LL, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low V<sub>F</sub> Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC and secondary side applications, this ST SiC diode will boost the performance in hard switching conditions. This rectifier will enhance the performance of the targeted application. Its high forward surge capability ensures a good robustness during transient phases.



Product status				
STPSC15H12				
Product	summary			
I <sub>F(AV)</sub>	15 A			
V <sub>RRM</sub>	1200 V			
T <sub>j</sub> (max.)	175 °C			
V <sub>F</sub> (typ.)	1.35 V			

# 1 Characteristics

#### Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol		Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage ( $T_j$ =	itive peak reverse voltage (T <sub>j</sub> = -40 °C to +175 °C)			V
I <sub>F(RMS)</sub>	Forward rms current			38	Α
		TO-220AC, T <sub>C</sub> = 155 °C, D	OC current <sup>(1)</sup>		
I <sub>F(AV)</sub> Average forward current	DO-247 LL, , T <sub>C</sub> = 150 °C, DC current <sup>(1)</sup>		15	A	
Denetitive needs ferward every	TO-220AC, T <sub>C</sub> = 155 °C, T <sub>j</sub> = 175 °C, δ = 0.1		58		
IFRM	I <sub>FRM</sub> Repetitive peak forward current	DO -247 LL, $T_C$ = 150 °C, $T_j$ = 175 °C, $\delta$ = 0.1		61	A
	Surge non repetitive forward current		T <sub>C</sub> = 25 °C	105	
I <sub>FSM</sub>		T <sub>C</sub> = 150 °C	90	Α	
		t <sub>p</sub> = 10 μs square	T <sub>C</sub> = 25 °C	630	
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C
Tj	Operating junction temperature range			-40 to +175	°C

1. Value based on R<sub>th(j-c)</sub> max.

#### Table 2. Thermal parameters

Symbol	Parameter			Max. value	Unit
<b>R</b>	Junction to case	TO-220AC	0.45	0.6	°C/W
R <sub>th(j-c)</sub>		DO-247 LL	0.50	0.70	C/vv

For more information, please refer to the following application note:

AN5088 : Rectifiers thermal management, handling and mounting recommendations

#### Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>		T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	7.5	90	μA
IR () Reverse lea	Reverse leakage current	T <sub>j</sub> = 150 °C		-	45	600	
V <sub>F</sub> <sup>(2)</sup>	Forward valtage drap	T <sub>j</sub> = 25 °C	I_ = 15 A	-	1.35	1.50	V
VF	Forward voltage drop	T <sub>j</sub> = 150 °C	– I <sub>F</sub> = 15 A	-	1.75	2.25	V

1. Pulse test:  $t_p = 10 \text{ ms}, \delta < 2\%$ 

2. Pulse test:  $t_p = 500 \ \mu s, \ \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

 $P = 1.09 \text{ x } I_{F(AV)} + 0.0775 \text{ x } I_{F}^{2} (RMS)$ 

For more information, please refer to the following application notes related to the power losses:

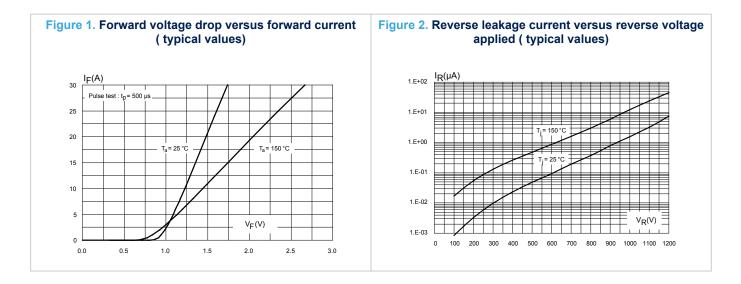
- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
Q <sub>Cj</sub> <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 800 V	-	94	-	nC	
C	C <sub>i</sub> Total capacitance	$V_{R}$ = 0 V, $T_{c}$ = 25 °C, F = 1 MHz	-	1200	-	_	
C <sub>j</sub> lota		$V_{R}$ = 800 V, $T_{c}$ = 25 °C, F = 1 MHz	-	78	-	pF	
		V <sub>R</sub>					

### Table 4. Dynamic electrical characteristics

Most accurate value for the capacitive charge:  $Q_{Cj}(V_R) = \int_{0}^{V_R} C_j(V) dV$ 

## 1.1 Characteristics (curves)



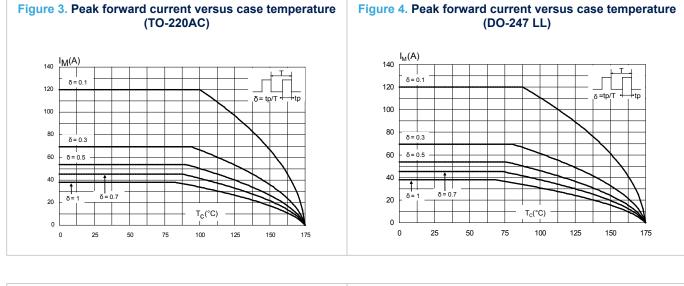


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

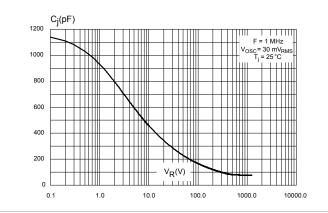
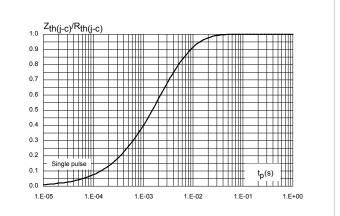
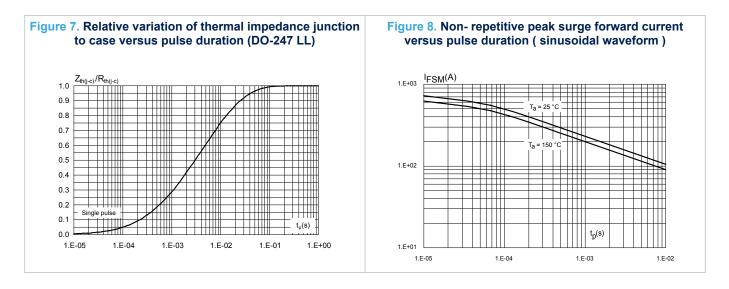
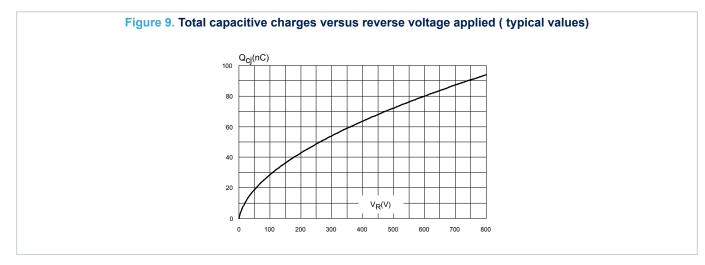


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC)







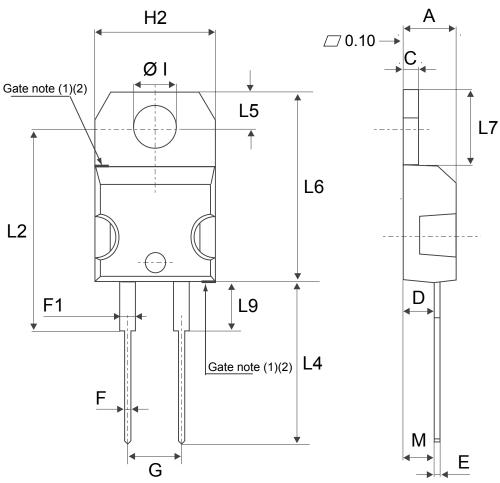


# 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

## 2.1 TO-220AC package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m



### Figure 10. TO-220AC package outline

(1) :Max resin gate protusion 0.5 mm

(2) :Resin gate position is accepted in each of the two positions shown on the drawings or their symmetrical

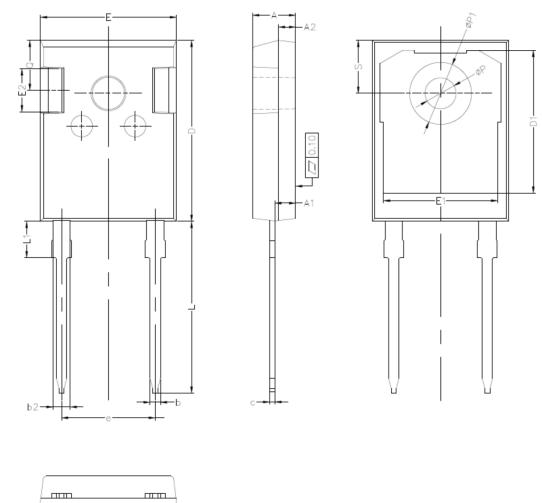
		Dimer	nsions		
Ref.	Millin	neters	Inches (for reference only)		
	Min.	Max.	Min.	Max.	
A	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
E	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
H2	10.00	10.40	0.393	0.409	
L2	16.4	0 typ.	0.64	5 typ.	
L4	13.00	14.00	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.60 typ. 0.102 typ.		2 typ.		
Diam	3.75	3.85	0.147	0.151	

### Table 5. TO-220AC package mechanical data



## 2.2 DO-247 LL package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 N·m
- Maximum torque value: 1.0 N·m



#### Figure 11. DO-247 LL package outline

*Note:* This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

		Dimer	nsions	
Ref.	Millim	neters	Inches (for re	ference only)
	Min.	Max.	Min.	Max.
А	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
С	0.38	0.89	0.015	0.035
D	20.80	21.46	0.819	0.845
D1	13.08		0.515	
E	15.49	16.26	0.610	0.640
е	10.88	3 typ.	0.4	28
E1	13.06		0.514	
E2	3.43	5.10	0.135	0.200
L	19.80	20.32	0.779	0.800
L1		4.50		0.177
Р	3.50	3.70	0.137	0.146
P1	7.00	7.40	0.275	0.292
Q	5.38	6.20	0.219	0.244
S	6.16	typ.	0.2	243

### Table 6. DO-247 LL package mechanical data



# **3** Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC15H12D	STPSC15H12D	TO-220AC	1.86 g	50	Tube
STPSC15H12WL	STPSC15H12WL	DO-247 LL	5.9 g	30	Tube

### Table 7. Ordering information

# **Revision history**

#### Table 8. Document revision history

Date	Revis ion	Changes
10-May-2016	1	Initial version
05-Sep-2017	2	Added DO-247 LL package.Updated Section "Features", Section 1:"Characteristics" and Table 8: "Ordering information".
03-Apr-2018	3	Updated Section 2.2 DO-247 LL package information.
23-Jun-2021	4	Added Section STPOWER, Section Sustainable technology and Applications. Updated Table 4 and Section 2.2 DO-247 LL package information.

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